

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	(channel near structure) near15 (vertical near fin) with (semiconductor near material)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/05 12:23
L2	1	(channel near structure) with (vertical near fin) with (semiconductor near material)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/05 12:23
L3	2	(channel near structure) with (vertical near fin) with (semiconductor or silicon or sige)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/05 12:24
L4	14	(channel near structure) and (vertical near fin) and (semiconductor or silicon or sige)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/05 12:25
L5	10	(channel near structure) and (vertical near fin) and (semiconductor or silicon or sige) near3 (material)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/05 12:27
L6	102	(channel near5 structure) and (vertical near3 fin) and (semiconductor or silicon or sige) near3 (material)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/05 12:27
L7	102	(channel near5 structure) and (vertical near3 fin) and (semiconductor or silicon or sige or silicon near germanium) near3 (material)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/05 12:27
L8	87	(channel near5 structure) and (vertical near3 fin) and (semiconductor or silicon or sige or silicon near germanium) near (material)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/05 12:27
L9	12	8 and (vertical near3 fin) with (semiconductor or sige or silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/05 12:31

L10	3	(vertical near3 fin) with (planar near3 fin) with (semiconductor or sige or silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/05 12:32
L11	3	(vertical near3 fin) with (planar near3 fin) with (semiconductor or sige or silicon near germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/05 12:32
L12	11	(vertical near3 fin) with (planar near3 fin) and (semiconductor or sige or silicon near germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/05 12:34
L13	43	(vertical near3 fin) and (planar near3 fin) and (semiconductor or sige or silicon near germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/05 12:34
L14	3	13 and (vertical near3 fin) with (insulat\$3 or dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/05 12:35
L15	1	13 and (vertical near3 fin) with (nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/05 12:35